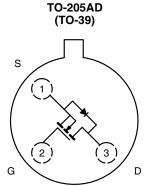
2N6661, 2N6661-2, 2N6661JANTX, 2N6661JANTXV

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N-Channel 90 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	90				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	4				
Configuration	Single				



Top View

FEATURES

- · Military Qualified
- Low On-Resistence: 3.6 Ω
- Low Threshold: 1.6 V
- Low Input Capacitance: 35 pF
- Fast Switching Speed: 6 ns
- Low Input and Output Leakage

BENEFITS

- Guaranteed Reliability
- Low Offset Voltage
- Low-Voltage Operation
- · Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Hi-Rel Systems
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ORDERING INFORMATION					
PART	PACKAGE	DESCRIPTION/DSCC PART NUMBER	VISHAY ORDERING PART NUMBER		
2N6661		Commercial	2N6661		
		Commercial, Lead (Pb)-free	2N6661-E3		
2N6661-2	See -2 Flow Document		2N6661-2		
2N6661JANTX	TO-205AD	JANTX2N6661 (std Au leads)	2N6661JTX02		
	(TO-39)	JANTX2N6661 (with solder)	2N6661JTXL02		
		JANTX2N6661P (with PIND)	2N6661JTXP02		
2N6661JANTXV		JANTXV2N6661 (std Au leads)	2N6661JTXV02		
		JANTXV2N6661P (with PIND)	2N6661JTVP02		

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V_{DS}	90				
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I-	0.86	А		
	T _C = 100 °C	l _D	0.54			
Pulsed Drain Current ^a	I _{DM}	3				
Maximum Power Dissipation	T _C = 25 °C	P_{D}	6.25	W		
	T _A = 25 °C	- PD	0.725	vv		
Thermal Resistance, Junction-to-Ambient ^b		R _{thJA}	170	°C/W		
Thermal Resistance, Junction-to-Case	R _{thJC}	20				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

Notes

- a. Pulse width limited by maximum junction temperature.
- b. Not required by military spec.



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SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)								
					LIMITS			
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.b	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 10 \mu\text{A}$		90	125	-		
		$V_{DS} = V_{GS}, \ I_D = 1 \ mA$ $T_A = -55 \ ^{\circ}C$ $T_A = 125 \ ^{\circ}C$		0.8	1.6	2	V	
Gate-Source Threshold Voltage	$V_{GS(th)}$			-	1.8	2.5		
				T _A = 125 °C	0.3	1.3	-	
Gate-Body Leakage	loss	$V_{GS} = \pm 20 \text{ V}$ $V_{DS} = 0 \text{ V}$		s = 0 V	-	-	± 100	20
Gate-body Leakage	I _{GSS}	VGS - ± 20 V		T _A = 125 °C	-	-	± 500	nA
Zero Gate Voltage Drain Current	l- o o	V _{GS} = 0 V	V _{DS} =	= 72 V	-	-	1	μA
Zero Gate Voltage Drain Gurrent	I _{DSS}			T _A = 125 °C	-	-	100	
On-State Drain Current ^b	I _{D(on)}	V _{GS} = 10 V	V_{DS}	= 10 V	-	1.8	-	mA
		$V_{GS} = 5 V$	I _D =	$I_D = 0.3 A$		3.8	5.3	Ω
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V	I _D = 1 A		-	3.6	4	
			V _{GS} = 10 V		T _A = 125 °C ^d	-	6.7	7.5
Forward Transconductanceb	9 _{fs}	V _{DS} =	_{DS} = 7.5 V, I _D = 0.475 A		170	340	-	mS
Diode Forward Voltage	V_{SD}	V _{GS} = 0 V	I _S = 0.86 A		0.7	0.9	1.4	V
Dynamic								
Input Capacitance	C _{iss}		_{SS} = 0 V V _{DS} = 25 V, f = 1 MHz		-	35	50	- pF
Output Capacitance	Coss	V - 0 V			-	15	40	
Reverse Transfer Capacitance	C _{rss}	v _{GS} = 0 v			-	2	10	
Drain-Source Capacitance	C _{ds}			-	30	-		
Switching ^c								
Turn-On Time	t _{ON}	$V_{DD} = 25 \text{ V, } R_L = 23 \ \Omega$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 23 \ \Omega$		23 Ω	-	6	10	
Turn-Off Time	t _{OFF}			-	8	10	ns	

Notes

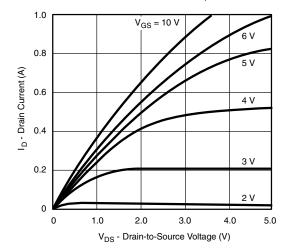
- a. FOR DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW \leq 300 μ s duty cycle \leq 2 %.
- c. Switching time is essentially independent of operating temperature.
- d. This parameter not registered with JEDEC.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2N6661, 2N6661-2, 2N6661JANTX, 2N6661JANTXV

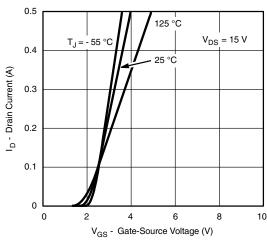
Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

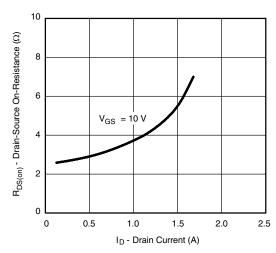


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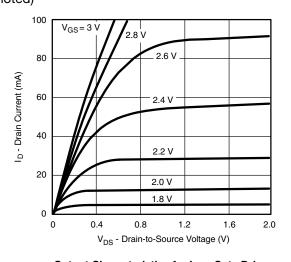
Ohmic Region Characteristics



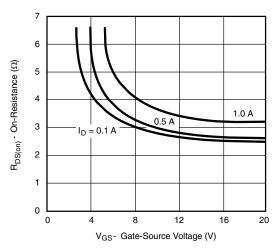
Transfer Characteristics



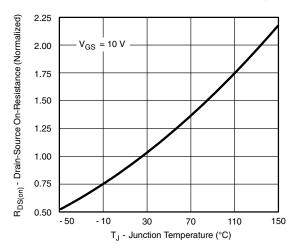
On-Resistance vs. Drain Current



Output Characteristics for Low Gate Drive



On-Resistance vs. Gate-to-Source Voltage

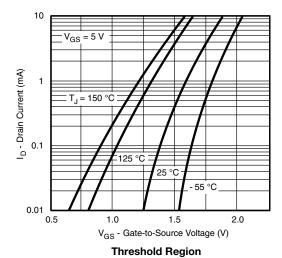


Normalized On-Resistance vs. Junction Temperature

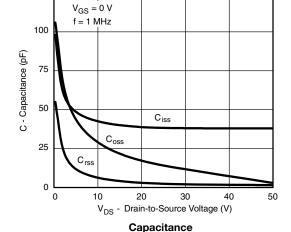
125

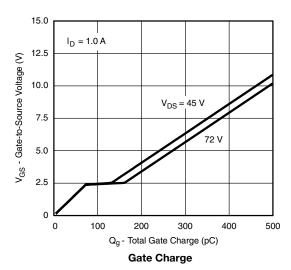
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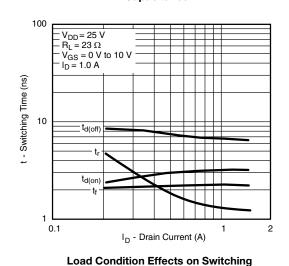
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

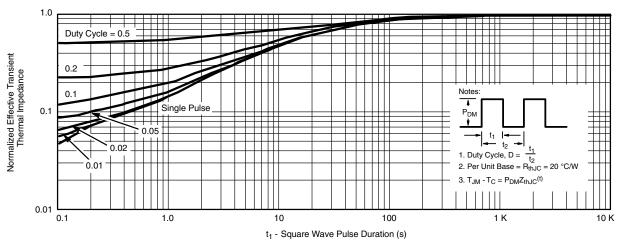


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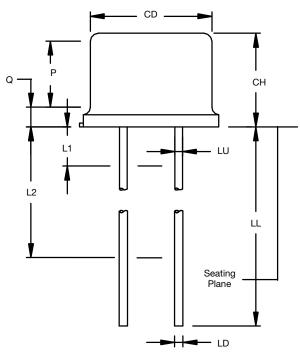


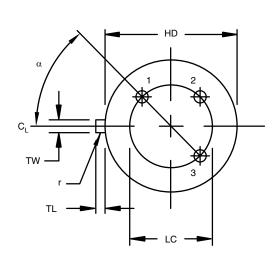
Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg270225.



TO-205AD (TO-39 TALL LID)





DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
CD	0.305	0.335	7.75	8.51	
CH	0.240	0.260	6.10	6.60	
HD	0.335	0.370	8.51	9.40	
LC ⁽⁶⁾	0.200) TP	5.08	3 TP	
LD ⁽⁷⁾⁽⁸⁾	0.016	0.021	0.41	0.53	
LL (7)(8)	0.500	0.750	12.70	19.05	
LU (7)(8)	0.016	0.019	0.41	0.48	
L1 ⁽⁷⁾⁽⁸⁾	_	0.050	_	1.27	
L2 ⁽⁷⁾⁽⁸⁾	0.250	_	6.35	_	
P (5)	0.100	_	2.54	_	
Q ⁽⁴⁾	_	0.050	_	1.27	
r ⁽⁹⁾	_	0.010	_	0.25	
TL ⁽³⁾	0.029	0.045	0.74	1.14	
TW ⁽²⁾	0.028	0.034	0.71	0.86	
α (6)	45° TP		45°	TP	

ECN: S15-1675-Rev. D, 27-Jul-15

DWG: 5511

Notes

- (1) Dimensions are in inches. Metric equivalents are given for general information only.
- (2) Beyond radius (r) maximum, TW shall be held for a minimum length of 0.011" (0.028 mm).
- (3) Dimension TL measured from maximum HD.
- (4) Outline in this zone is not controlled.
- (5) Dimension CD shall not vary more than 0.010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
- (6) Leads at guage plane 0.054" + 0.001", 0.000" (1.37 mm + 0.03 mm, 0.00 mm) below seating plane shall be within 0.007" (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- (7) LU applies between L1 and L2, LD applies between L2 and L maximum. Diameter is uncontrolled in L1 and beyond LL minimum.
- (8) All three leads.
- (9) Radius (r) applies to both inside corners of tab.
- $^{(10)}$ Drain is electrically connected to the case.

Revison: 27-Jul-15 1 Document Number: 71367



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000



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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.